

InGaAs Avalanche Photodiode (APD) with Integrated Lens, 10 Gbps(Chip-on-Carrier)

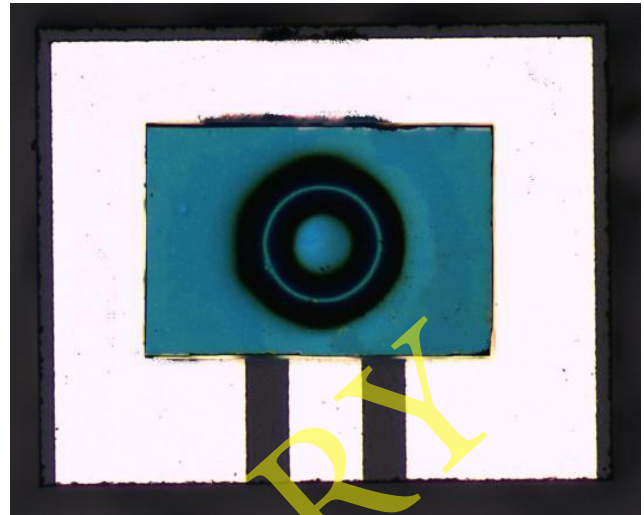
PDAB0022L-CC

Applications:

Long Haul Receivers
SONET/SDH Receivers

Features:

Ceramic sub-carrier
Integrated Lens
Planer Structure for High Reliability
1000 to 1625nm Spectral Response
Low Dark Current



Description:

Go!Foton's Avalanche Photodiode (APD) is suitable for 10 Gbps applications in optical communications. This InGaAs APD has a planer structure for high reliability. It has back illuminated structure. The optical signal goes through the integrated lens on the back surface.

Specifications:

Electro-Optical Characteristics:

Parameter	Min	Typ	Max	Conditions
Active Area Diameter (μm)		22		
Responsivity (A/W)	0.80			1.55 μm , M=1
Dark Current (nA)			50	0.9V _{br} , 25°C
Breakdown Voltage (V)	25		40	10 μA
Capacitance (pF)			0.3	1MHz, M=10
Frequency Response (GHz)	7			M=8, RL=50 Ω
Operating Voltage (V)			V _{br} -1	M=10
Punch-through Voltage (V)	12		V _{br} -7	
Temperature Coefficient of Vb (%/°C)			0.15	

- 1) Condition unless noted; 25°C, P_{out} = 1 μW
- 2) Punch-through voltage is defined as voltage where 1.5V above the voltage where the first deviation of IV curve under illumination shows local maximum.
- 3) Responsivity at punch-through voltage is defined as responsivity at M=1

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